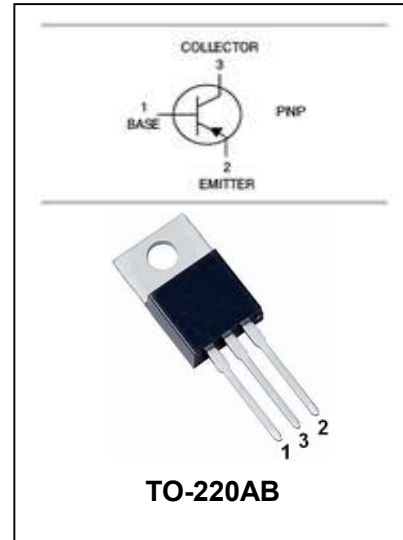


PNP Epitaxial Silicon Transistor

2SB861

FEATURES

- Low Frequency Power Amplifier Coloe
- TV Vertical Deflection Output Complementary
- Pair With 2SD1138.



MAXIMUM RATING operating temperature range applies unless otherwise specified

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-200	V
V_{CEO}	Collector-Emitter Voltage	-150	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current	Continuous Peak	A
		-2 -5	
P_C	Collector Dissipation	$T_a=25^{\circ}\text{C}$ $T_c=25^{\circ}\text{C}$	W
		1.8 30	
T_j, T_{stg}	Junction and Storage Temperature	-45 to +150	$^{\circ}\text{C}$

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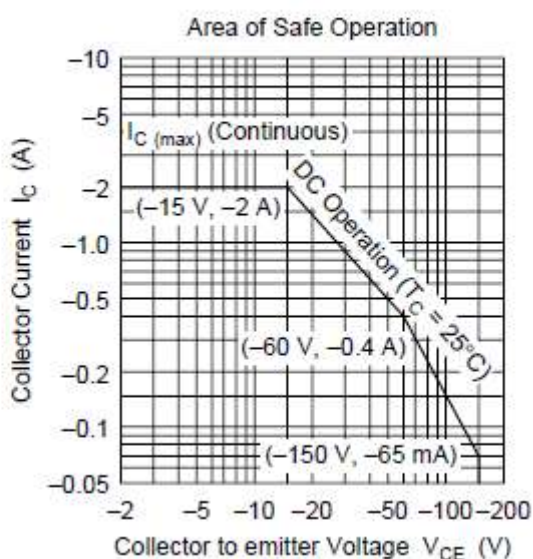
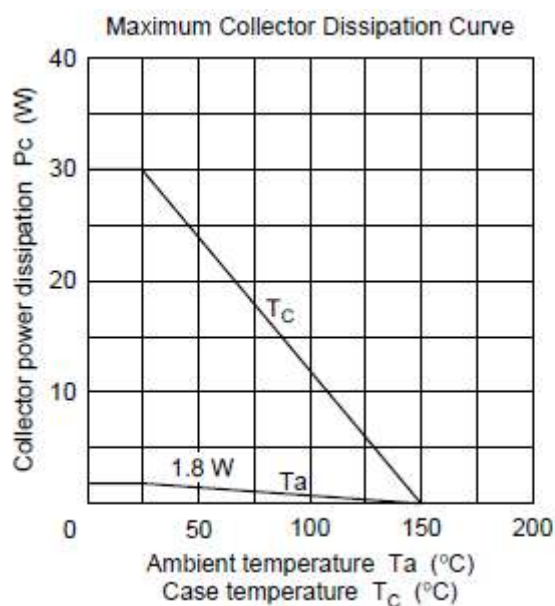
ELECTRICAL CHARACTERISTICS Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	Test conditions	MIN	Typ	MAX	UNIT
Collector-base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -50\text{mA}, I_E = 0$	-150			V
Emitter-base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -5\text{mA}, I_C = 0$	-6			V
Collector Cut-off Current	I_{CBO}	$V_{CB} = -120\text{V}, I_E = 0$			-1	μA
DC Current Gain	h_{FE}	$V_{CE} = -4\text{V}, I_C = -50\text{mA}$	60		200	
		$V_{CE} = -10\text{V}, I_C = -500\text{mA}$	60			
Collector-emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -500\text{mA}, I_B = -50\text{mA}$			-3	V
Base-emitter On Voltage	$V_{BE(on)}$	$I_C = -50\text{mA}, V_{CE} = -4\text{V}$			-1	V
Collector Output Capacitance	C_{ob}	$V_{CB} = -100\text{V}, I_E = 0$ $f = 1\text{MHz}$		30		pF

CLASSIFICATION OF h_{FE}

Range	B	C
Marking	60-120	100-200

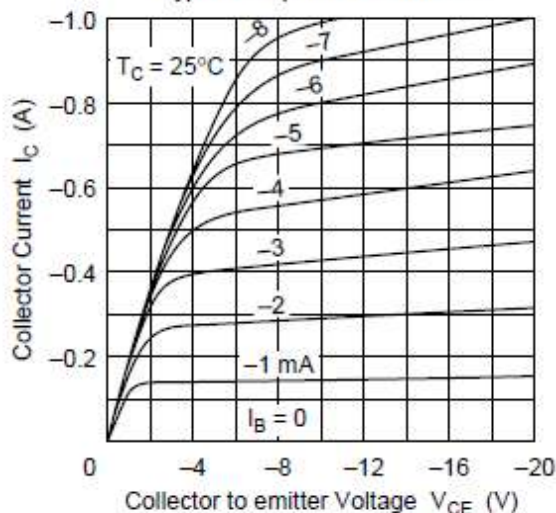
TYPICAL CHARACTERISTICS @ $T_a = 25^\circ\text{C}$ unless otherwise specified



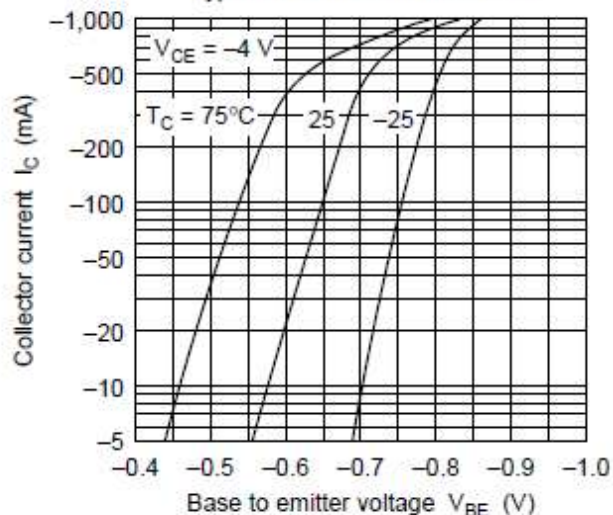
PNP Epitaxial Silicon Transistor

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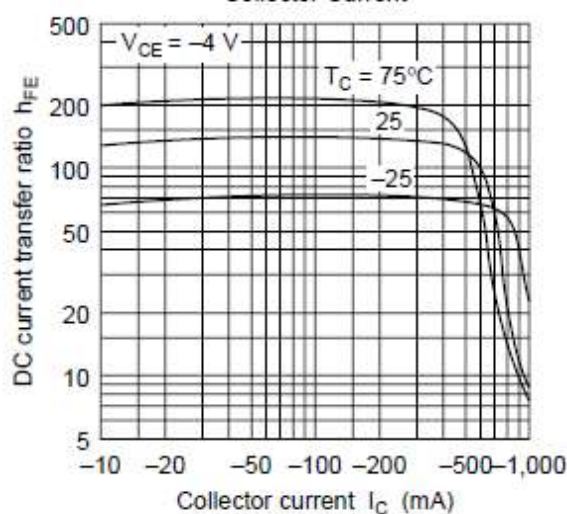
Typical Output Characteristics



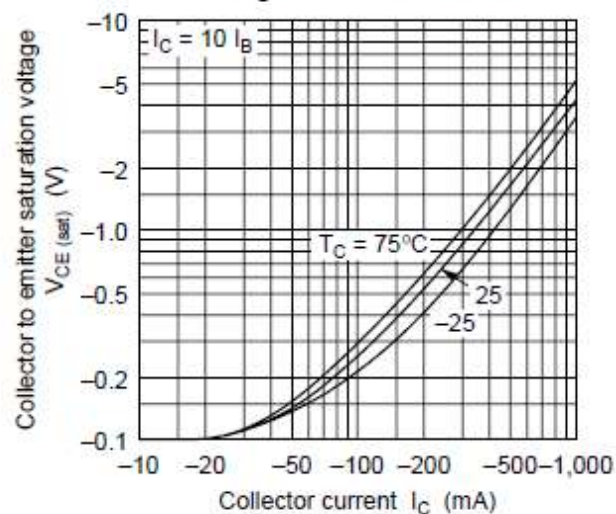
Typical Transfer Characteristics



DC Current Transfer Ratio vs. Collector Current



Collector to Emitter Saturation Voltage vs. Collector Current



PNP Epitaxial Silicon Transistor

2SB861

PACKAGE OUTLINE

Plastic surface mounted package

TO-220AB

